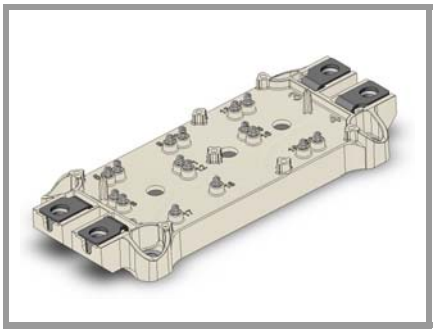
SEMiX553GAR128Ds



SEMiX® 3s

SPT IGBT Modules

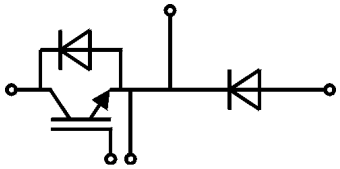
SEMiX553GAR128Ds

Features

- Homogeneous Si
- SPT = Soft-Punch-Through technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability
- UL recognised file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic welders up to 20 kHz



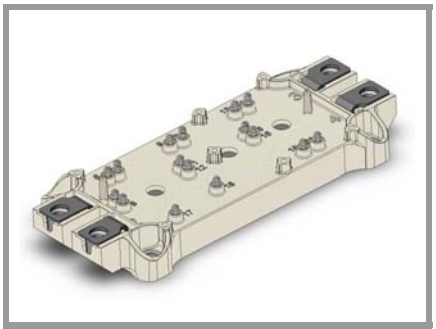
GAR

Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
IGBT				
V_{CES}			1200	V
I_C	T_j = 150 °C	T_c = 25 °C	533	A
		T_c = 80 °C	379	A
I_{Cnom}			300	A
I_{CRM}	I_{CRM} = 2xI_{Cnom}		600	A
V_{GES}			-20 ... 20	V
t_{psc}	V_{CC} = 600 V $V_{GE} \leq$ 20 V $V_{CES} \leq$ 1200 V	T_j = 125 °C	10	µs
T_j			-40 ... 150	°C
Inverse diode				
I_F	T_j = 150 °C	T_c = 25 °C	421	A
		T_c = 80 °C	289	A
I_{Fnom}			300	A
I_{FRM}	I_{FRM} = 2xI_{Fnom}		600	A
I_{FSM}	t_p = 10 ms, sin 180°, T_j = 25 °C		2300	A
T_j			-40 ... 150	°C
Freewheeling diode				
I_F	T_j = 150 °C	T_c = 25 °C	521	A
		T_c = 80 °C	347	A
I_{Fnom}			300	A
I_{FRM}	I_{FRM} = 2xI_{Fnom}		600	A
I_{FSM}	t_p = 10 ms, sin 180°, T_j = 25 °C		2300	A
T_j			-40 ... 150	°C
Module				
$I_{t(RMS)}$			600	A
T_{stg}			-40 ... 125	°C
V_{isol}	AC sinus 50Hz, t = 1 min		4000	V

Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
$V_{CE(sat)}$	I_C = 300 A V_{GE} = 15 V chiplevel	T_j = 25 °C		1.9	2.35	V
		T_j = 125 °C		2.1	2.55	V
V_{CE0}		T_j = 25 °C		1	1.15	V
		T_j = 125 °C		0.9	1.05	V
r_{CE}	V_{GE} = 15 V	T_j = 25 °C		3.0	4.0	mΩ
		T_j = 125 °C		4.0	5.0	mΩ
$V_{GE(th)}$	V_{GE}=V_{CE}, I_C = 12 mA		4.5	5	6.5	V
I_{CES}	V_{GE} = 0 V	T_j = 25 °C		0.1	0.3	mA
	V_{CE} = 1200 V	T_j = 125 °C				mA
C_{ies}	V_{CE} = 25 V V_{GE} = 0 V	f = 1 MHz		28.3		nF
C_{oes}		f = 1 MHz		1.86		nF
C_{res}		f = 1 MHz		1.17		nF
Q_G	V_{GE} = - 8 V...+ 15 V			2880		nC
R_{Gint}	T_j = 25 °C			1.33		Ω



SEMiX® 3s

SPT IGBT Modules

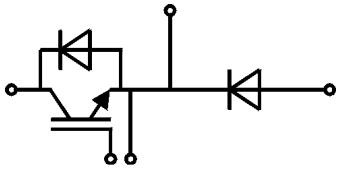
SEMiX553GAR128Ds

Features

- Homogeneous Si
- SPT = Soft-Punch-Through technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability
- UL recognised file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic welders up to 20 kHz



GAR

Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
$t_{d(on)}$	V_{CC} = 600 V	T_j = 125 °C		185		ns
t_r	I_C = 300 A	T_j = 125 °C		65		ns
E_{on}	$R_{G\ on}$ = 3 Ω	T_j = 125 °C		27		mJ
$t_{d(off)}$	$R_{G\ off}$ = 3 Ω	T_j = 125 °C		635		ns
t_f		T_j = 125 °C		80		ns
E_{off}		T_j = 125 °C		33		mJ
$R_{th(j-c)}$	per IGBT				0.061	K/W
Inverse diode						
$V_F = V_{EC}$	I_F = 300 A; V_{GE} = 0 V; chip	T_j = 25 °C		2.0	2.50	V
		T_j = 125 °C		1.8	2.3	V
V_{F0}		T_j = 25 °C	0.75	1.1	1.45	V
		T_j = 125 °C	0.5	0.85	1.2	V
r_F		T_j = 25 °C	2.5	3.0	3.5	mΩ
		T_j = 125 °C	2.7	3.2	3.7	mΩ
I_{RRM}	I_F = 300 A; di/dt_{off} = 5400 A/µs; V_{GE} = -15 V; V_{CC} = 600 V	T_j = 125 °C		325		A
Q_{rr}		T_j = 125 °C		46		µC
E_{rr}		T_j = 125 °C		17		mJ
$R_{th(j-c)}$	per diode				0.11	K/W
Freewheeling diode						
$V_F = V_{EC}$	I_F = 300 A; V_{GE} = 0 V; chip	T_j = 25 °C		2.0	2.5	V
		T_j = 125 °C		1.8	2.3	V
V_{F0}		T_j = 25 °C	0.75	1.1	1.45	V
		T_j = 125 °C	0.5	0.85	1.2	V
r_F		T_j = 25 °C	2.5	3.0	3.5	mΩ
		T_j = 125 °C	2.7	3.2	3.7	mΩ
I_{RRM}	I_F = 300 A; di/dt_{off} = 5400 A/µs; V_{GE} = -15 V; V_{CC} = 600 V	T_j = 125 °C		325		A
Q_{rr}		T_j = 125 °C		46		µC
E_{rr}		T_j = 125 °C		17		mJ
$R_{th(j-c)}$	per diode				0.11	K/W
Module						
L_{CE}				20		nH
$R_{CC'+EE'}$	res., terminal-chip	T_C = 25 °C		0.7		mΩ
		T_C = 125 °C		1		mΩ
$R_{th(c-s)}$	per module			0.04		K/W
M_s	to heat sink (M5)		3		5	Nm
M_t		to terminals (M6)	2.5		5	Nm
						Nm
w					300	g
Temperatur Sensor						
R_{100}	T_c=100°C (R_{25}=5 kΩ)			493 ± 5%		Ω
$B_{100/125}$	$R_{(T)}=R_{100}\exp[B_{100/125}(1/T-1/T_{100})]$; T[K];			3550 ±2%		K

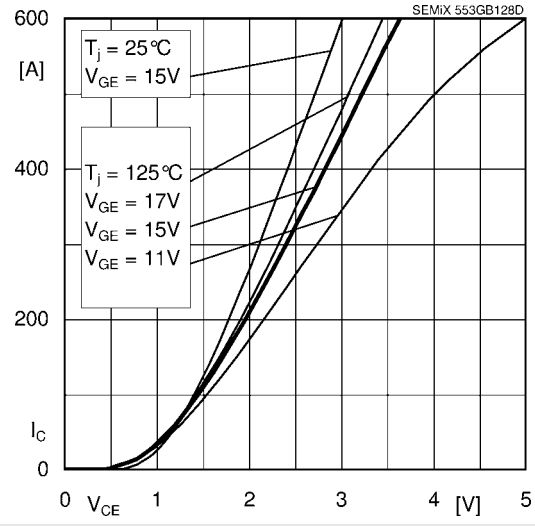


Fig. 1: Typ. output characteristic, inclusive $R_{CC'+EE'}$

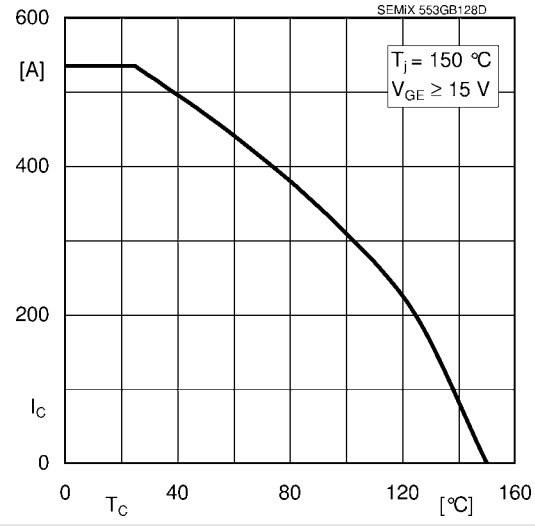


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

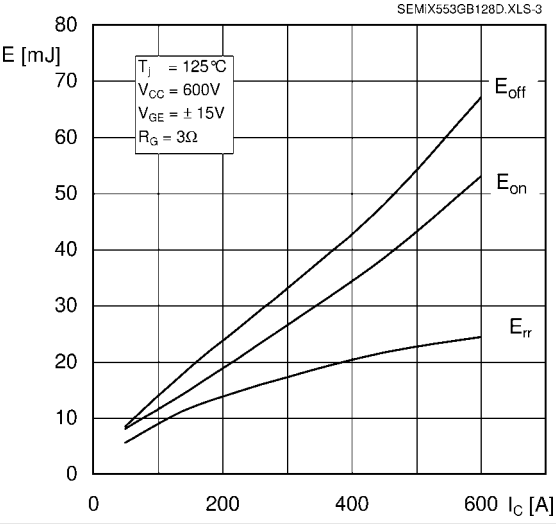


Fig. 3: Typ. turn-on /-off energy = f (I_C)

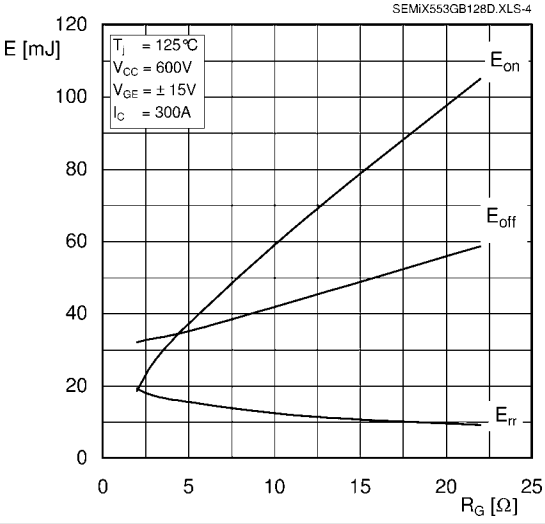


Fig. 4: Typ. turn-on /-off energy = f (R_G)

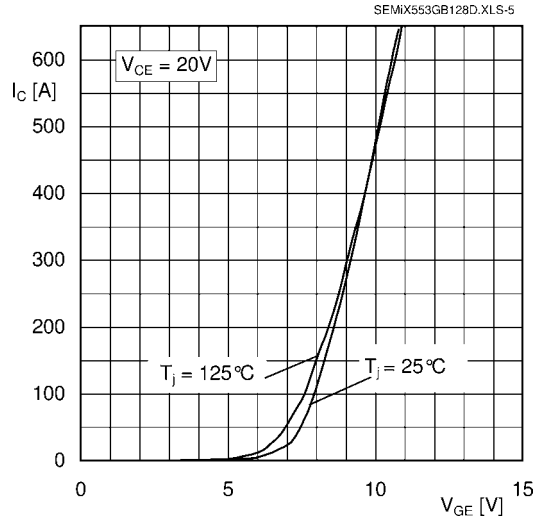


Fig. 5: Typ. transfer characteristic

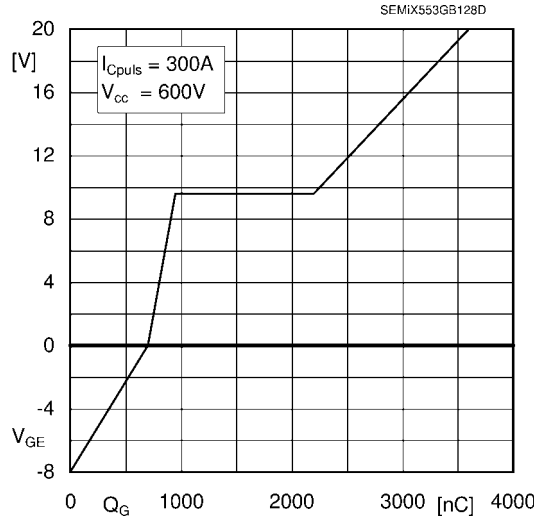


Fig. 6: Typ. gate charge characteristic

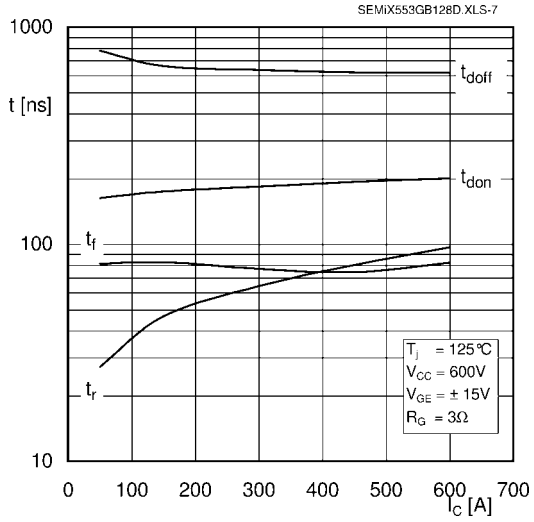


Fig. 7: Typ. switching times vs. I_C

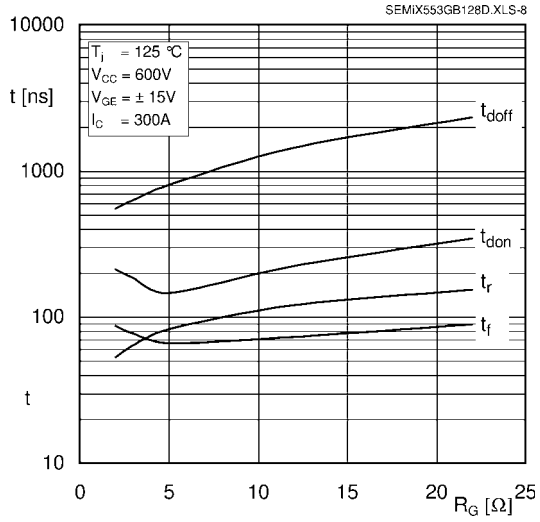


Fig. 8: Typ. switching times vs. gate resistor R_G

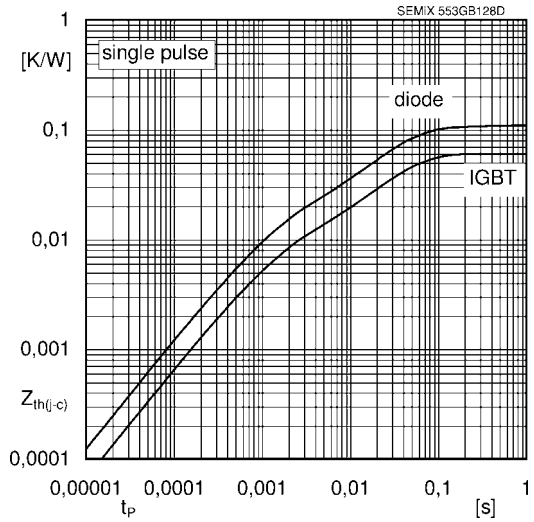


Fig. 9: Typ. transient thermal impedance

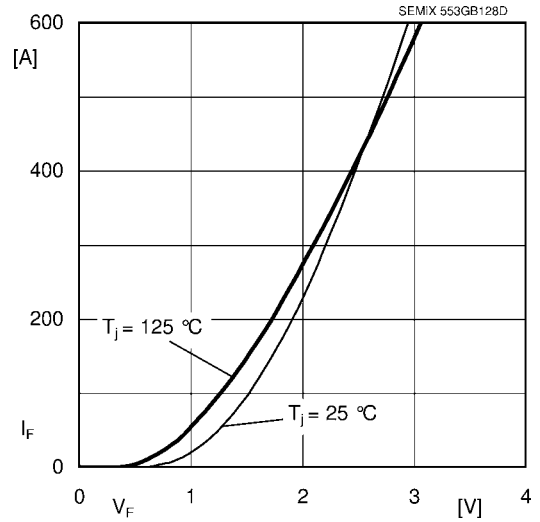


Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC'+EE'}$

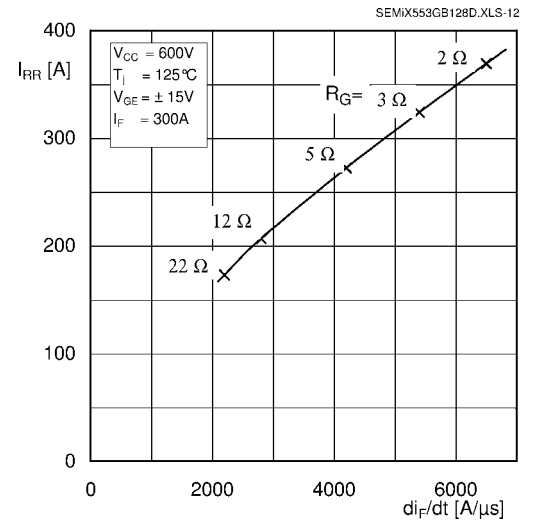


Fig. 11: Typ. CAL diode peak reverse recovery current

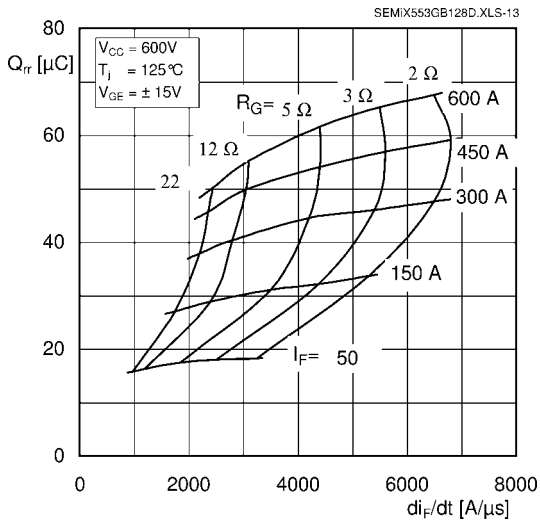
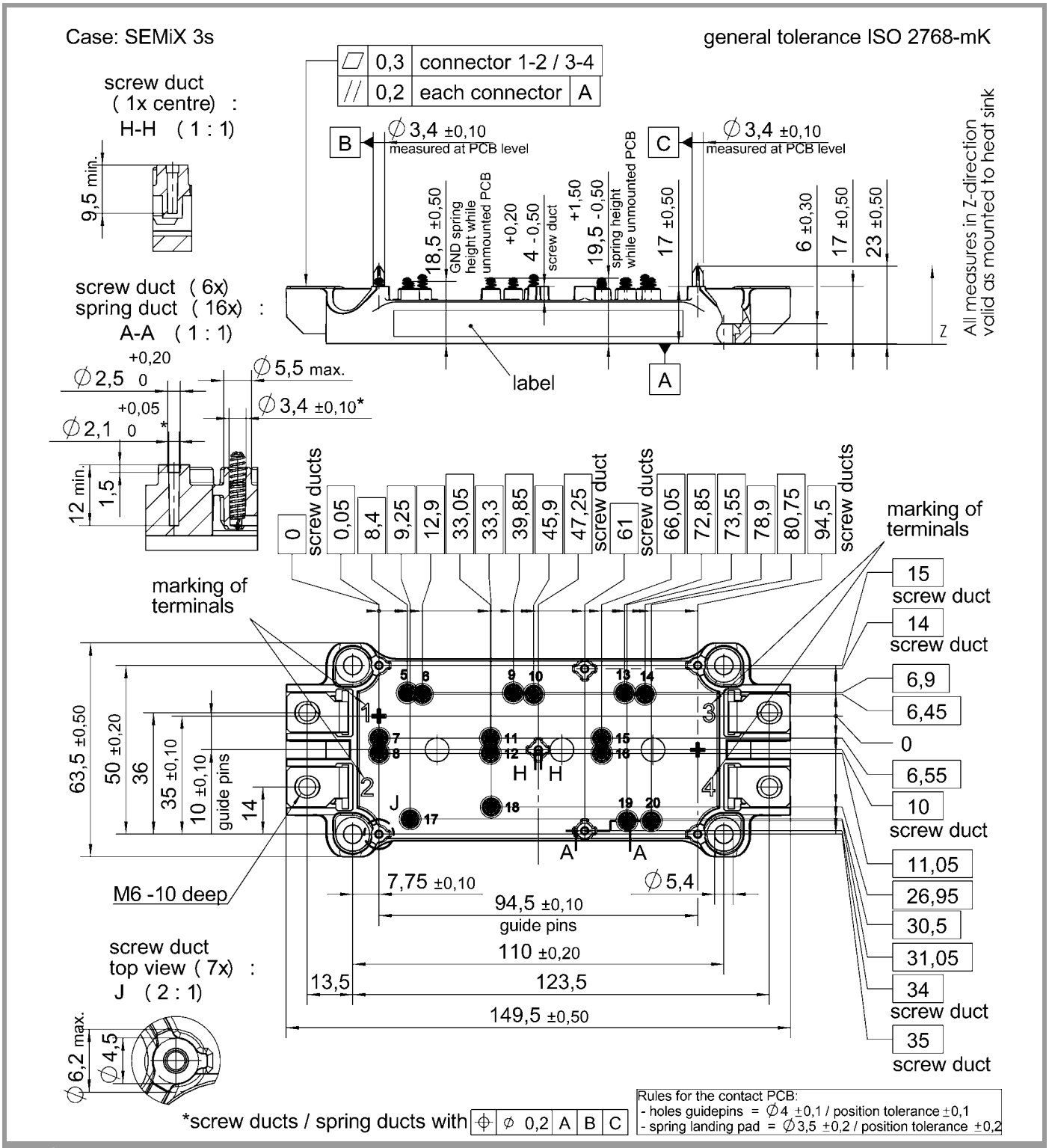
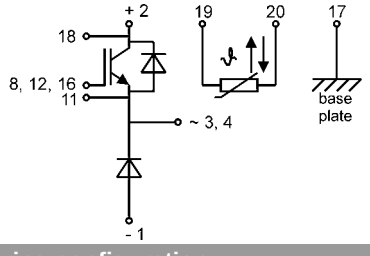


Fig. 12: Typ. CAL diode recovery charge



SEMiX 3s



spring configuration

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

